



silicon products

RESEARCH ENGINEERING PRODUCTION

Cost effective low stress float zone  
silicon feed rods made from Siemens  
reactor chemical vapor deposition

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GEFÖRDERT VOM



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## Silicon Products Bitterfeld GmbH & Co. KG

[www.silicon-products-gmbh.com](http://www.silicon-products-gmbh.com)

- engineering / consulting
- equipment for Siemens process technology
- silicon / slim rods
- chlorosilanes

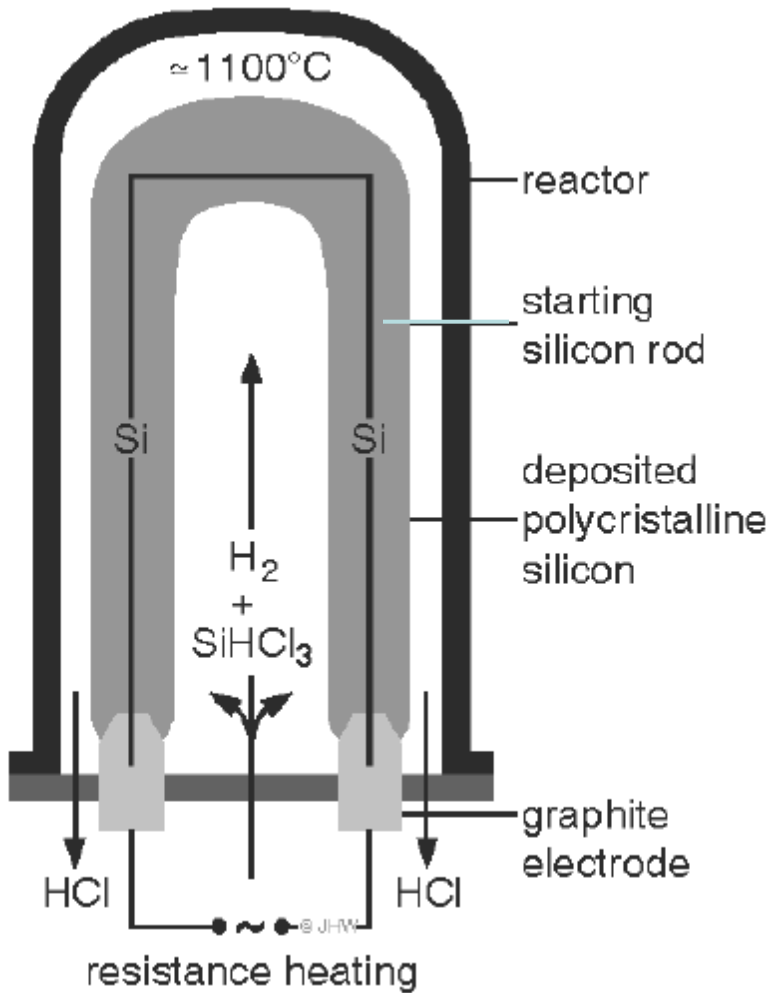
**Product:** high purity silicon

**Output Capacity:** 1.800 t/a

**Process Technology:** Siemens process

**Employees:** ca. 50



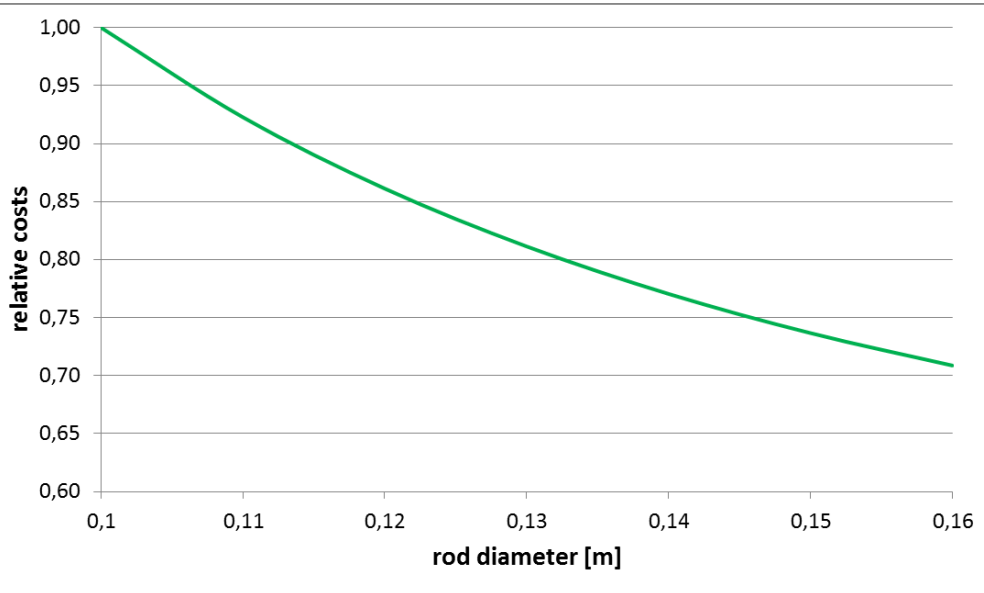


## Main Challenges

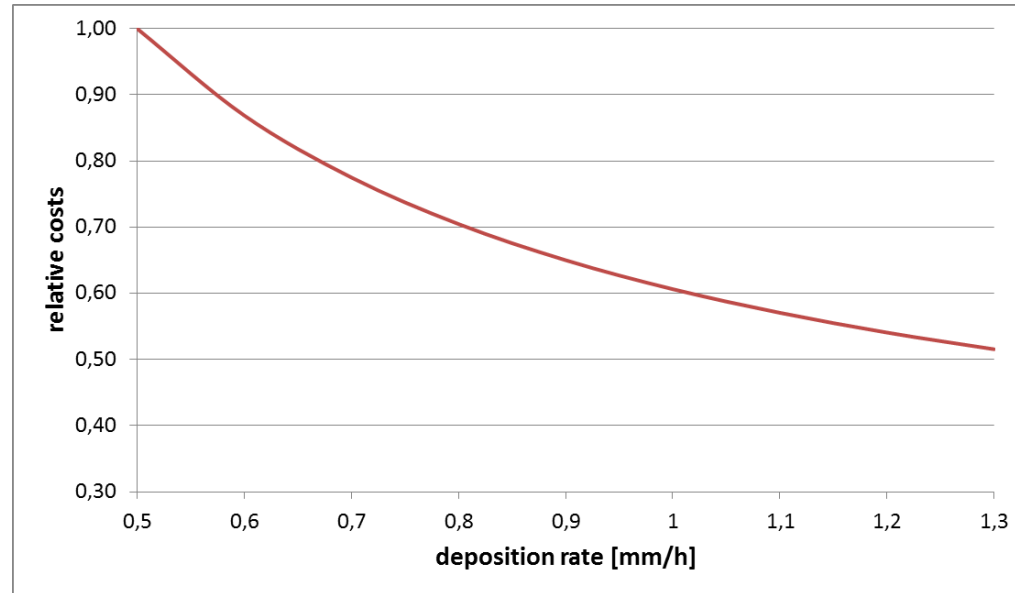
- **purity (dopants, metals, non-metals, particles)**  
→ crystal yield
- **low stress silicon**  
→ mass yield

# Cost Influence Parameters for Silicon FZ - Feedstock – “Process Engineer ´s View”

➤ final rod thickness and rod length



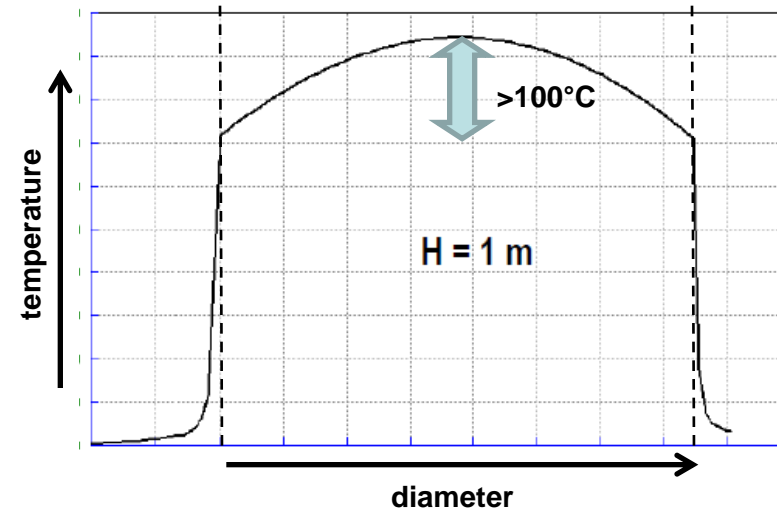
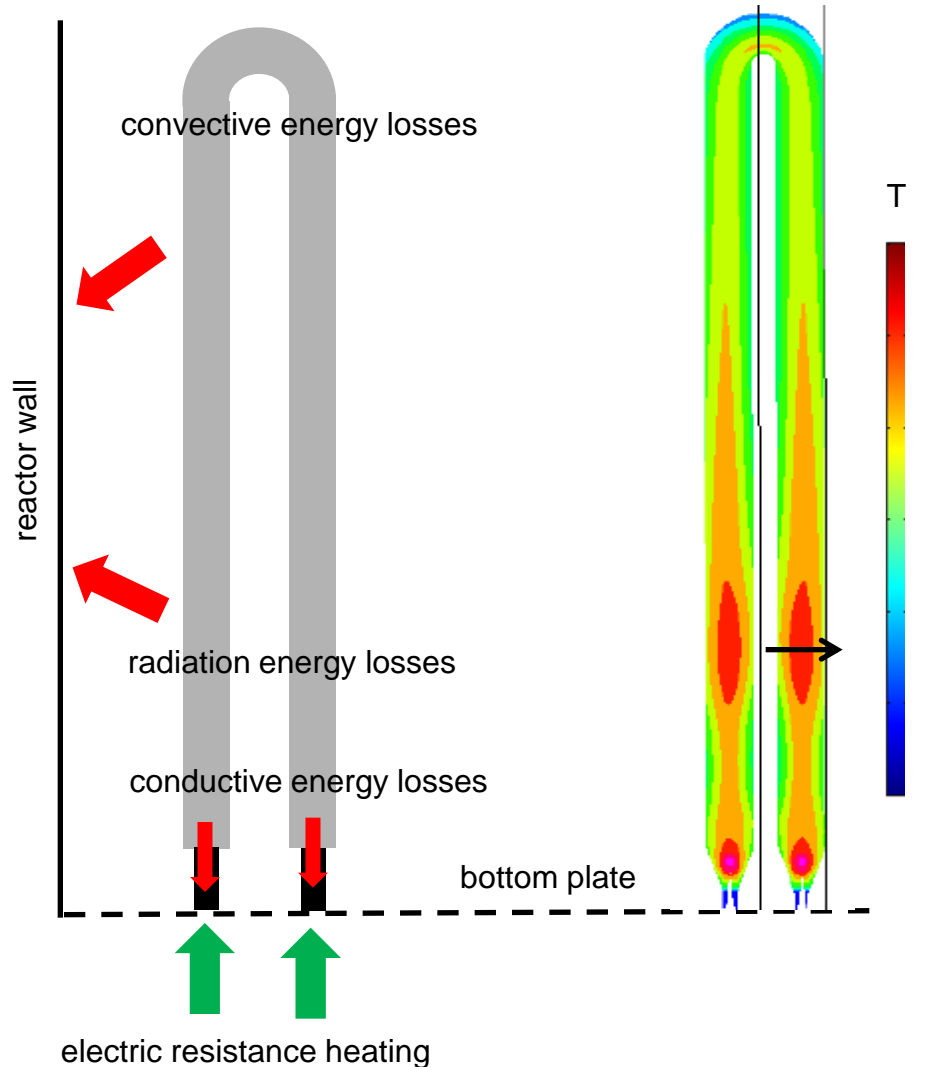
➤ deposition rate



Motivation: control and reduction of rod stresses

# How is Thermo-Mechanical Stress Formed?

## U-shaped polysilicon rod in the CVD reactor



non-linear temperature gradients during deposition and cool down

↓

thermo-mechanical stress after cool down

↓

breakage

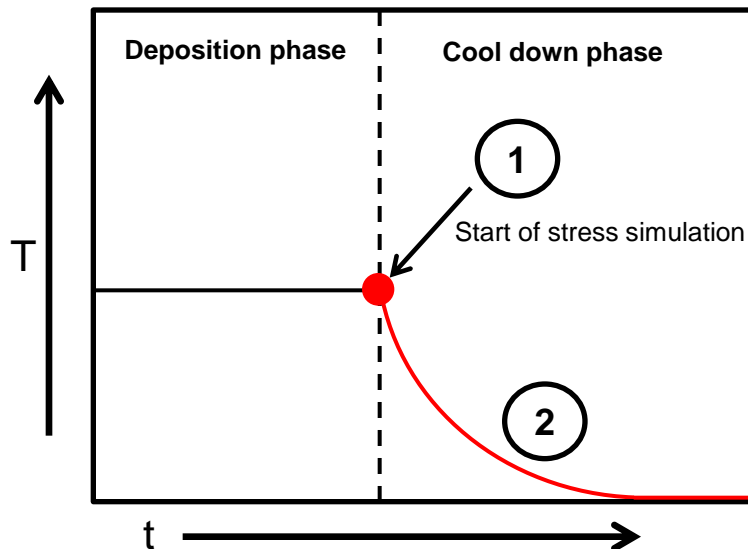
## Aim

- build up of an 2D model for stress calculation (FE)
  - calculation temperature distribution -> strain field -> stress field

## Basic Assumption

- stress is created during cool down phase.
- stress due to temperature gradients during deposition can mainly be released by plastic deformation.
  - $T > 1000^{\circ}\text{C}$

temperature curve of the rod surface



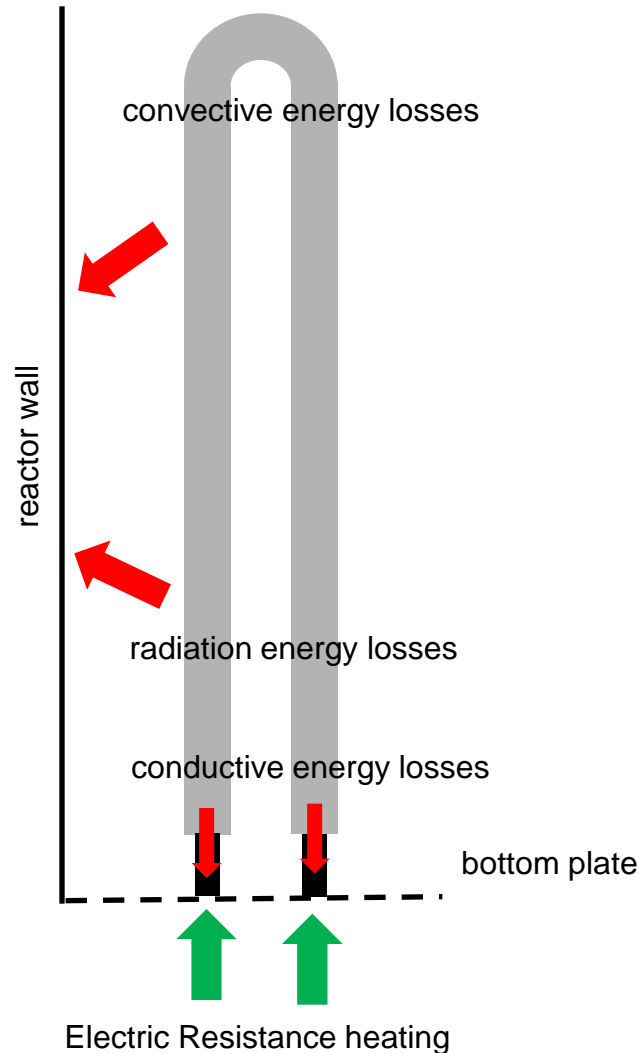
1

**temperature field constant – stationary process condition**  
constant gas flow, constant voltage and current, constant rod thickness

2

**temperature field changes**  
time dependent stress evolution

## U-shaped polysilicon rod in the CVD reactor



➤ very low temperature gradients by very low cooling rates

– reduction of convective energy losses

– reduction of radiation energy losses

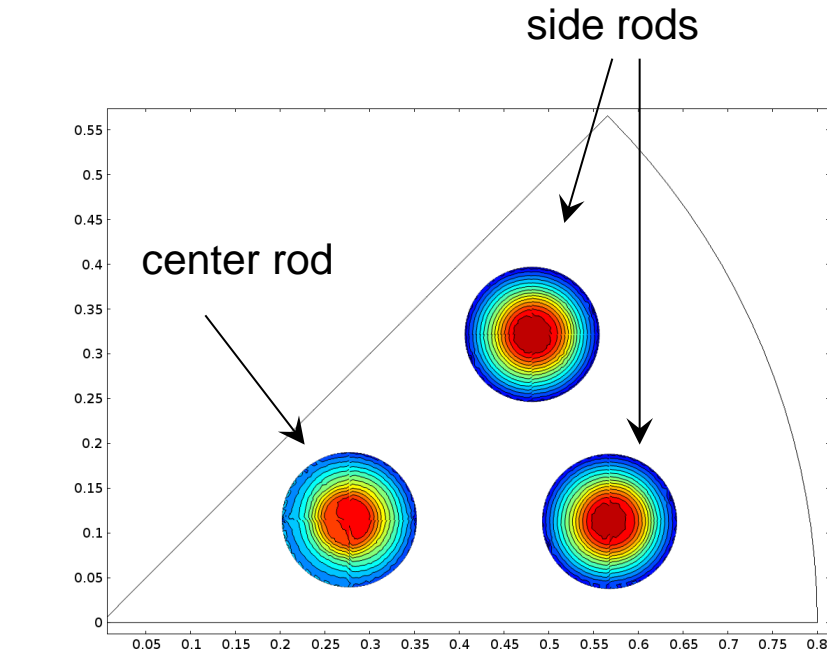
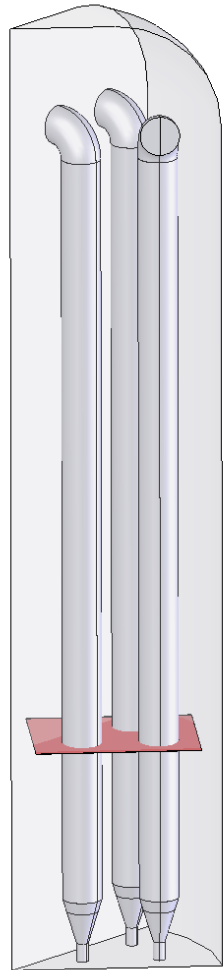
alternatively:

– external rod heating

– rise temperature before cool down

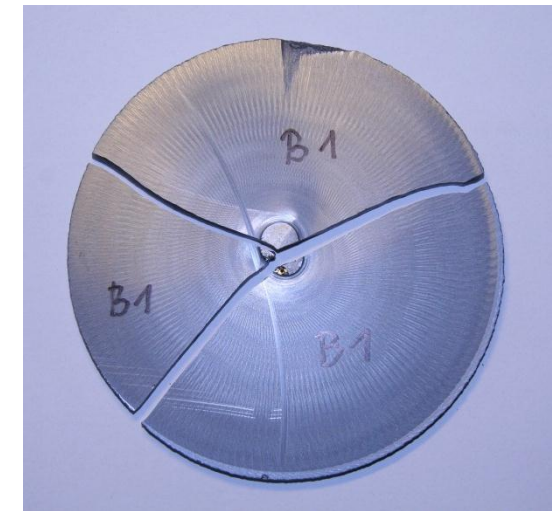
Tokuyama DE19780520B4

➤ calculated 2D stress field in a horizontal cut plane



H<sub>2</sub> atmosphere benchmark during cool down (diameter = 150mm, 7 bars, temperature before cool down ~1100°C)

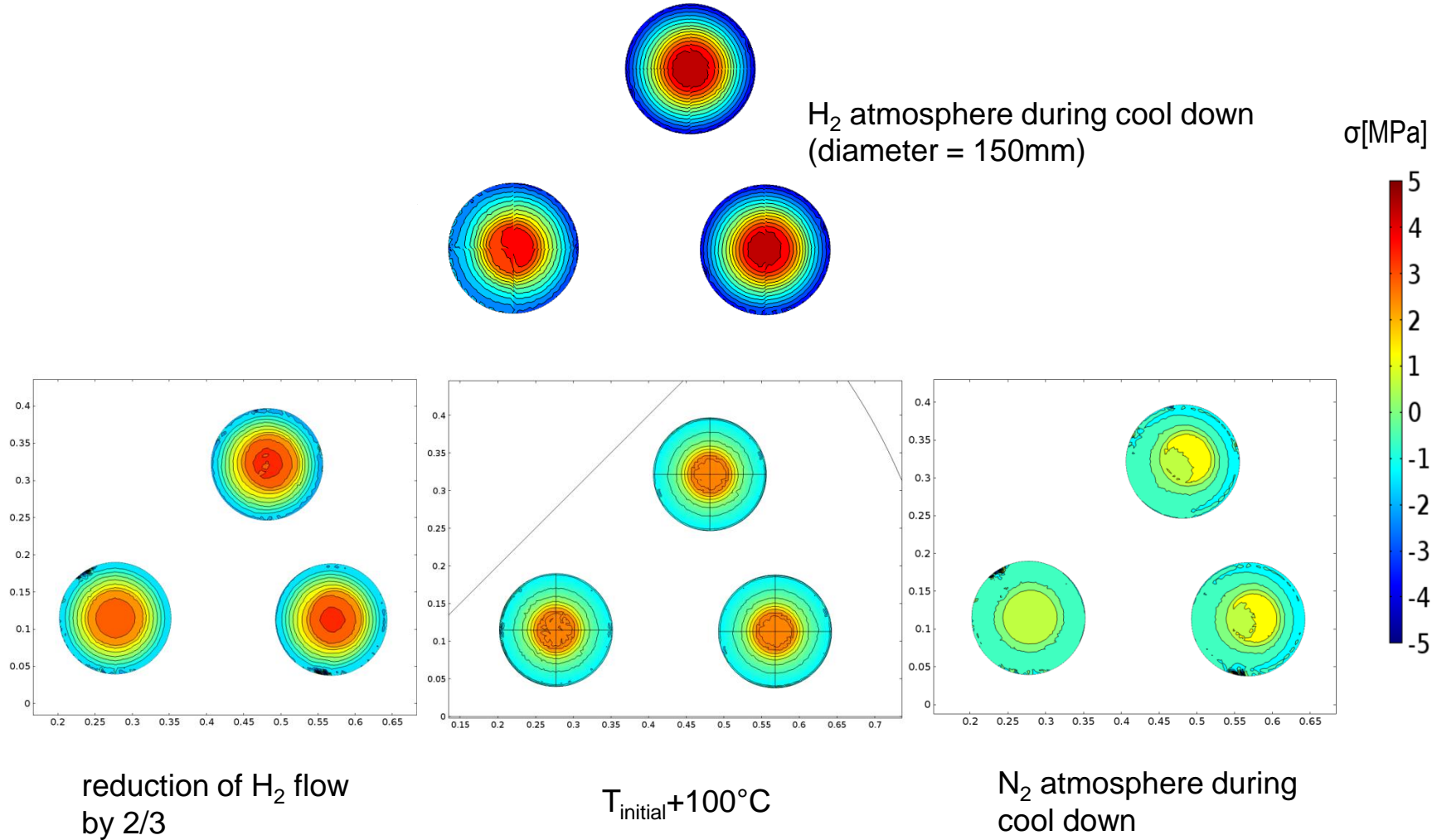
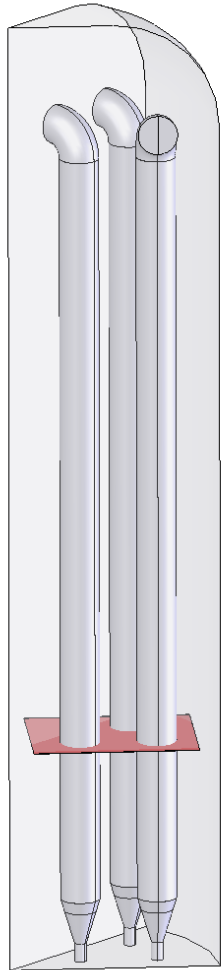
- compressive stresses (blue) near surface
- tensile stress (red) in rod center which leads to breakage

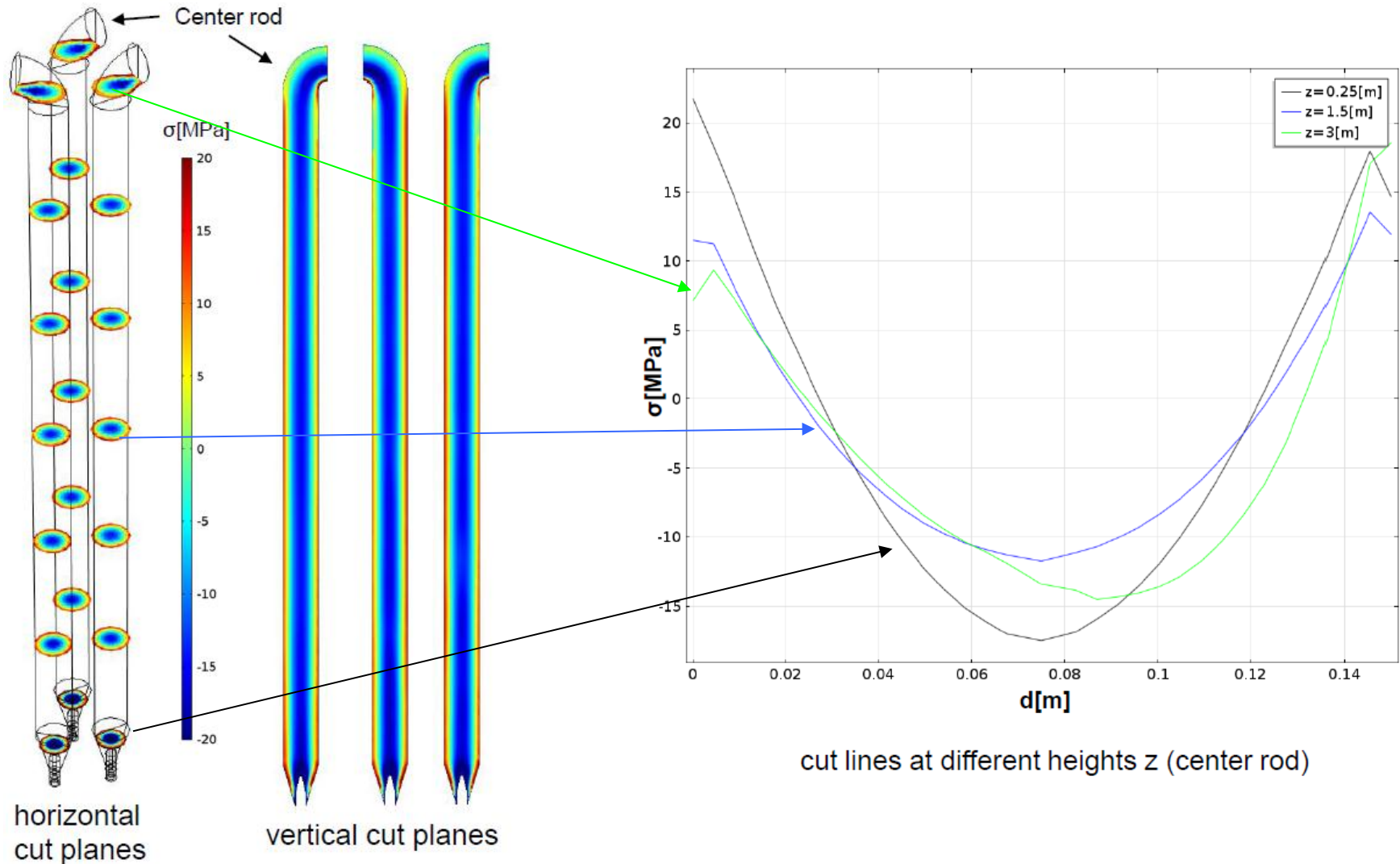


- inner rods have lower stress on surface and in the center



➤ calculated 2D stress field in a horizontal cut plane





- high tensile (blue) stresses close to the electrode and the bridge

- Main operation cost factors are final rod thickness, rod length, growth rate and rod stress.
- Development of an 2D model for simulation of residual rod stress was carried out.
- Rod stress can strongly be reduced by reducing conductive losses.
- The inner ring is expected to have lower rod stresses.
- The electrode and bridge regions are most critical for stresses and cracks.





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